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# Structures and stabilities of small silicon clusters: *Ab initio* molecular-orbital calculations of Si<sub>7</sub>-Si<sub>11</sub>

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Ab initio all-electron molecular-orbital calculations have been carried out to study the structure and relative stability of small silicon clusters ( $Si_n$ , n=7-11). A number of low-energy geometric isomers are optimized at the second-order Møller-Plesset (MP2) MP2/6-31G(d) level. Harmonic vibrational analysis has been performed to assure that the optimized geometries are stable. The total energies of stable isomers are computed at the coupled-cluster single and double substitutions (including triple excitations) [CCSD(T)] CCSD(T)/6-31G(d) level. The calculated binding energies per atom at both the MP2/6-31G(d) and CCSD(T)/6-31G(d) levels agree with the experiments. For Si<sub>7</sub>, Si<sub>8</sub>, and Si<sub>10</sub>, the lowest-energy structures are the same as those predicted previously from the all-electron optimization at the Hartree-Fock (HF) HF/6-31G(d) level [Raghavachari and Rohlfing, J. Chem. Phys. 89, 2219 (1988)]. For Si<sub>9</sub>, the lowest-energy isomer is same as that predicted based on density-functional plane-wave pseudopotential method [Vasiliev, Ogut, and Chelikowsky, Phys. Rev. Lett. 78, 4805 (1997)]. Particular attention has been given to Si<sub>11</sub> because several low-energy geometric isomers were found nearly isoenergetic. On the basis of MP2/6-311G(2d)//CCSD(T)/6-311G(2d) calculation, we identified that the  $C_{2v}$  isomer, a tricapped trigonal prism with two additional caps on side trigonal faces, is most likely the global-minimum structure. However, another competitive geometric isomer for the global minimum is also found on basis of the MP2/6-311G(2d)//CCSD(T)/6-311G(2d) calculation. Additionally, calculations of the binding energy and the cluster polarizability offer more insights into relatively strong stability of two magic-number clusters Si<sub>6</sub> and Si<sub>10</sub>. © 2003 American Institute of Physics. [DOI: 10.1063/1.1535906]

#### I. INTRODUCTION

Since the advent of advanced laser vaporization techniques<sup>1-6</sup> semiconductor atomic and nanoclusters have become an active subject of research, both experimentally and theoretically. <sup>1–50</sup> A great deal of understanding has been obtained on this microscopic form of matter, for example, their selectivity, stability, and reactivity, and their evolution toward the bulk matter. Silicon atomic and nanoclusters have been extensively studied because of their relevance to the development of nanoelectronics.<sup>7-9</sup> In particular, spectroscopic studies of atomic silicon clusters have been carried out by many groups. <sup>10–22</sup> Photoelectron spectroscopy of silicon anion clusters 10 indicates that silicon clusters with 4, 6, 7, and 10 atoms are closed-shell clusters. Photodissociation of silicon cation clusters  $^{11,12}$  demonstrates  $\mathrm{Si}_n^+$  fragmentation products are mainly  $\mathrm{Si_6}^+ - \mathrm{Si_{11}}^+$ . Several photodissociation <sup>13–15</sup> and collision-induced dissociation <sup>16–18</sup> experiments have shown that Si<sub>6</sub> and Si<sub>10</sub> have exceptional stability, consistent with their "magic number" (particularly abundant) behavior in the mass spectra of Si clusters. 19 The Raman<sup>20</sup> and infrared<sup>21</sup> spectroscopy experiments have been utilized to infer the most stable structures of small silicon clusters. Mobility measurements<sup>22,23</sup> have also provided evidences of various stable isomers. Note that all these spectroscopic measurements provide only indirect information on the structures of small silicon clusters. Nevertheless, spectroscopic measurements have motivated considerable theoretical and computational studies on the microscopic silicon clusters.

In principle, ab initio molecular-orbital theory can provide direct structural information of the clusters. However, it is known that the number of stable geometric isomers of a cluster (local minima in the potential energy surface) increases exponentially with the number of atoms in the cluster.<sup>5</sup> As such, determination of the globalminimum structure is a challenging problem. 22,24 A series of systematic theoretical studies of small silicon clusters using all-electron molecular-orbital methods have been carried out by Raghavachari, Rohlfing, and their coworkers. 21,25-30 Quantum Monte Carlo simulation, <sup>31</sup> density-functional plane-wave pseudopotential methods, <sup>22,32–34,39–42</sup> and other quantum mechanical means <sup>35–38,43–46</sup> have also been employed by many groups to investigate various properties of silicon clusters and search for their global-minimum structures. Raghavachari and Logovinsky<sup>25</sup> were apparently the first to use all-electron molecular-orbital methods to calculate energies of small silicon clusters (Si<sub>2</sub>-Si<sub>6</sub>) and identify their lowest-energy geometries. Later, Raghavachari and Rohlfing<sup>27–30</sup> studied larger silicon clusters, Si<sub>7</sub>–Si<sub>11</sub>. They performed geometry optimization of several low-energy geometric isomers of Si<sub>7</sub>-Si<sub>10</sub> at the HF/6-31G(d) level, followed by a total-energy calibration at the second-order Møller-Plesset (MP2), MP3, and MP4 levels with the polarized 6-31G(d) basis set.<sup>27</sup> The structures, bonding properties, and relative stability of Si<sub>7</sub>-Si<sub>10</sub> clusters have been

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reported. In the cases of  $\mathrm{Si}_{10}$  and  $\mathrm{Si}_{11}$ , more detailed study of several low-energy geometric isomers was undertaken at higher MP4 or quadratic configuration-interaction [QCISD(T)] levels.  $^{28-30}$  For  $\mathrm{Si}_{7}\mathrm{-Si}_{11}$ , other theoretical methods have also been employed to search for their lowest-energy structures.  $^{21,26-31,35-45}$  Note that for  $\mathrm{Si}_{11}$ , there is still some uncertainty on the global-minimum structure due to sensitivity of low-energy structures and their energies to the selected theoretical methods (e.g., levels of theory and basis sets).

The aim of this work is to reexamine a number of lowenergy geometric isomers of  $Si_7-Si_{11}$  that have been reported previously at the Hartree-Fock (HF) or densityfunctional levels of theory. We have used all-electron molecular-orbital methods with including electron correlation effects in the determination of the cluster geometry. The geometry optimization is at the MP2/6-31G(d) level followed by the calibration of total energy at the CCSD(T)/6-31G(d) level. It is found that the electron correlation  $^{47}$  can sometimes have qualitative effects on the cluster geometry as some previously obtained stable isomers at the HF level can became unstable at the MP2 level. This study also provides some additional insight into the relative stability of two magic-number clusters of silicon.

#### II. COMPUTATIONAL DETAILS

We used the Møller–Plesset perturbation to the second order  $^{51-53}$  with a polarized 6-31G(d) basis set, i.e., the MP2/6-31G(d) level, to optimize the geometry of a number of low-energy isomers of  $\mathrm{Si}_7 - \mathrm{Si}_{11}$ . Correlation effects of all electrons in the clusters are thus taken into account approximately. For the geometry optimization, the Berny algorithm  $^{54}$  in the GAUSSIAN 98 software  $^{55}$  is employed. This algorithm is designed to locate the local minimum but not the global minimum. Hence, a careful choice of initial isomeric structures of the cluster is important to seek possible candidate for the global-minimum isomer.

In this work, most geometric isomers of  $\mathrm{Si}_7 - \mathrm{Si}_{11}$  are taken from previously obtained by other groups on basis of either the HF level of theory or plane-wave pseudopotential techniques. To obtain the local-minimum structure unbiasly, first, a full geometry optimization without constraining the cluster symmetry is undertaken at the MP2/6-31G(d) level. Second, the initial structures are optimized again with keeping the point-group symmetry of the clusters. Once the optimized structures are obtained from both approaches, the harmonic vibrational frequencies are then computed to examine possible appearance of any imaginary frequencies, that is, to examine whether the optimized structures are stable. Finally, for those stable isomers, their total energy is evaluated at the CCSD(T)/6-31G(d) level.  $^{52,56-58}$ 

#### **III. RESULTS AND DISCUSSIONS**

Figure 1 displays the optimized geometries of several low-energy geometric isomers of  $\mathrm{Si}_7\mathrm{-}\mathrm{Si}_{11}$ , where the silicon atoms are connected with a "bond" when the Si-Si interatomic distance is less than 3.0 Å. The bond lengths are listed in Table I. In a benchmark calculation at the

MP2/6-31G(d) level, the Si–Si bond length of Si<sub>2</sub> and Si<sub>2</sub>H<sub>6</sub> are 2.26 and 2.34 Å, respectively, whereas the experimental values are 2.25 and 2.33 Å.<sup>25</sup> This test calculation indicates that the relative percentage error of the calculated Si–Si bond length is less than 0.5%. Table II lists the calculated harmonic vibrational frequencies, IR intensities, and zero-point energy (ZPE). No imaginary frequencies were found for most of low-energy geometric isomers of Si<sub>7</sub>–Si<sub>11</sub>, at least at the MP2/6-31G(d) level of theory. Tables III and IV present the binding energies per atom at both the MP2/6-31G(d) and CCSD(T)/6-31G(d) levels, together with the experimental values. As shown in Fig. 2, there is a good correlation between the calculated and the measured binding energies.

#### A. Structure

#### 1. N=7

For  $Si_7$  we have examined a number of low-energy geometric isomers as those studied by Raghavachari and Rohlfing.<sup>27</sup> No qualitative change in the geometry of these isomers is found except the capped trigonal prism, which no longer is a local minimum at the MP2/6-31G(d) level. The lowest-energy isomer of  $Si_7$  is 7a, a *pentagonal bipyrimid* with  $D_{5h}$  symmetry, in agreement with the experiment<sup>20</sup> and previous theoretical studies.<sup>27,28,35,36,39,42</sup> Note that the pentagonal bipyrimid ( $D_{5h}$ ) is also the global minimum structure of the argon cluster<sup>24</sup> with seven atoms. Note also that the structures of small silicon clusters are different from the tetrahedral coordination characteristic of bulk silicon.

#### 2. N=8

In the case of Si<sub>8</sub>, full geometry optimizations at the MP2/6-31G(d) level followed by the total-energy calculation at the CCSD(T)/6-31G(d) level suggest that the isomer 8a, a distorted bicapped octahedron (capping two opposite faces) with  $C_{2h}(^1A_g)$  point group, is the lowest-energy structure.  $^{27,28,36,39,42}$  Raghavachari and Rohlfing  $^{27}$  have reported seven low-energy isomers of Si<sub>8</sub> on the basis of the HF/6-31G(d) level. Among the seven, six geometric isomers, i.e.,  $8a(C_{2h}, {}^{1}A_{g})$ ,  $8b(C_{2v}, {}^{1}A_{1})$ ,  $8d(C_{2v}, {}^{1}A_{1})$ ,  $8e(D_{3d}, {}^{3}A_{1g})$ ,  $8f(C_{3v}, {}^{3}A_{2})$ , and  $8g(C_{s}, {}^{1}A')$  have the same structure as ours despite of some differences in energy ordering and geometric parameters due to different levels of theory. However, the bicapped-trigonal-prism  $C_{2v}$  isomer shown in Ref. 27 is no longer a local minimum due to the appearance of several imaginary frequencies at the MP2/6-31G(d) level. Indeed, the full geometry optimization of the bicapped-trigonal-prism isomer yielded a new local-minimum structure (8c, with  $C_2$  symmetry). The isomer 8c could be viewed as a distorted 8a. Like the globalminimum isomer 8a, the isomer 8h with  $D_{2d}$  symmetry is also a distorted bicapped octahedron but the caps are on adjacent faces. Our calculation indicates that 8h is a relatively high- energy local minimum at the MP2/6-31G(d) level. 8h was previously thought to be the global minimum based on a semiempirical method. 43 The isomer 8g, a singly-

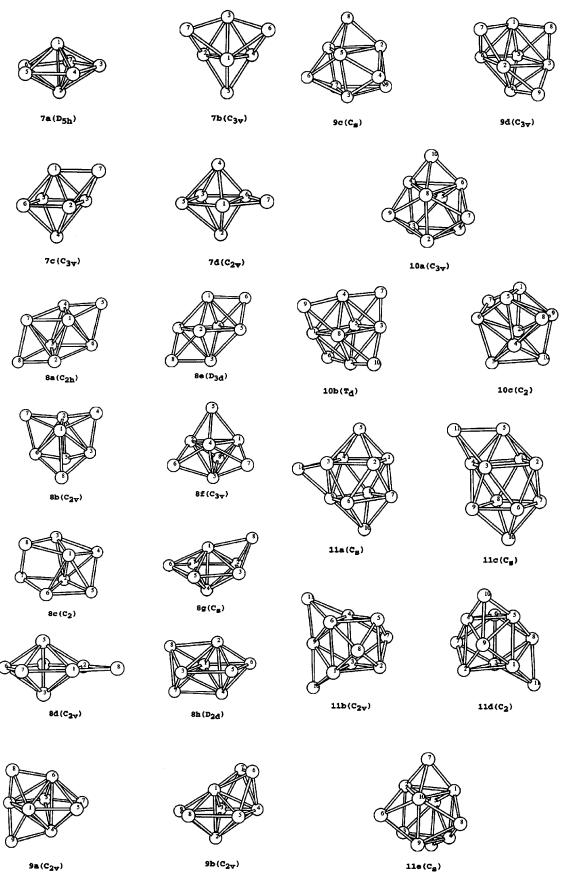


FIG. 1. Geometries of the low-energy isomer structures of  $Si_7 - Si_{11}$  at the MP2/6-31G(d) level [11e at the MP2/6-311(2d) level].

capped pentagonal bipyramid, was also previously thought to be the global minimum based on the tight-binding molecular dynamics calculation.  $^{35}$ 

#### 3. N=9

For  $Si_9$ , the global-minimum isomer appears to be the  $9a(C_{2v}, {}^1A_1)$ , whose structure has been viewed as *two* 

TABLE I. Optimized geometry parameters for (a) low-energy geometric isomers of  $Si_7$ – $Si_{11}$  at the MP2/6-31G(d) level and (b) three low-energy isomers of  $Si_{11}$  at the MP2/6-311(2d) level.

Cluster	Isomer	PG (State)	Bond len	gth (Å)	Cluster	Isomer	PG (State)	Bond lengt	h (Å)
(a)								$Si_2-Si_8$	2.373
Si <sub>7</sub>	7 a	$D_{5h}(^{1}A_{1}^{\prime})$						$Si_3-Si_8$	2.490
			$Si_1-Si_4$	2.458		8g	$C_s(^1A')$		
			$Si_3-Si_4$	2.483				$Si_1-Si_3$	2.508
	7 <i>b</i>	$C_{3v}(^{1}A_{1})$	$\mathrm{Si}_1\!-\!\mathrm{Si}_2$	2.512				$Si_1-Si_7$ $Si_1-Si_6$	2.524 2.386
	10	$C_{3v}(A_1)$	$Si_1 - Si_4$	2.485				$Si_1-Si_6$ $Si_1-Si_4$	2.380
			$Si_1-Si_4$ $Si_2-Si_4$	2.493				$Si_3-Si_4$	2.559
			$Si_1 - Si_7$	2.558				$Si_4-Si_7$	2.422
			$Si_2 - Si_7$	2.341				$Si_4 - Si_6$	2.532
	7 <i>c</i>	$C_{3v}(^{1}A_{1})$						$Si_2-Si_3$	2.897
			$Si_1-Si_7$	2.415				$Si_2-Si_7$	2.485
			$Si_1-Si_2$	2.452				$Si_6-Si_7$	2.440
			$Si_1-Si_6$	2.463				$Si_1-Si_8$	2.470
	7 <i>d</i>	$C_{2v}(^{1}A_{1})$	$\mathrm{Si}_4\mathrm{-}\mathrm{Si}_6$	2.555		8 <i>h</i>	$D_{2d}(^{1}A_{1})$	$Si_3-Si_8$	2.403
	7 a	$C_{2v}(A_1)$	$Si_1 - Si_7$	2.293		on	$D_{2d}(A_1)$	$Si_1-Si_7$	2.343
			$Si_1 - Si_6$	2.926				$Si_1 - Si_2$	2.619
			$Si_1 - Si_5$	2.415				$Si_4-Si_7$	2.926
			$Si_1 - Si_4$	2.504				Si <sub>7</sub> -Si <sub>8</sub>	2.636
			$Si_3-Si_5$	2.315				$Si_2 - Si_4$	2.894
			$Si_4 - Si_5$	2.687	$Si_9$	9 <i>a</i>	$C_{2v}(^{1}A_{1})$		
Si <sub>8</sub>	8 <i>a</i>	$C_{2h}(^{1}A_{g})$						$Si_5-Si_7$	2.401
			$Si_1 - Si_4$	2.462				$Si_2-Si_3$	2.552
			$Si_4 - Si_6$	2.865				$Si_1-Si_2$	2.547
			$Si_1-Si_2$ $Si_2-Si_6$	2.399 2.750				$Si_3-Si_6$ $Si_6-Si_7$	2.529 2.391
			$Si_2-Si_6$ $Si_1-Si_5$	2.276				$Si_6 Si_7$ $Si_1 - Si_6$	2.757
			$Si_5 - Si_6$	2.454				$Si_1 - Si_8$	2.345
			$Si_1-Si_3$	2.802				$Si_4 - Si_9$	2.386
	8b	$C_{2v}(^{1}A_{1})$	. ,					$Si_4-Si_6$	2.976
			$Si_1-Si_6$	2.647		9b	$C_{2v}(^{1}A_{1})$		
			$Si_1-Si_2$	2.480				$Si_1-Si_4$	2.644
			$Si_6-Si_7$	2.359				$Si_1-Si_3$	2.541
			$Si_1 - Si_7$	2.384 2.376				$Si_1-Si_7$ $Si_1-Si_2$	2.370 2.644
			$Si_6 - Si_8$ $Si_1 - Si_8$	2.656				$Si_1-Si_2$ $Si_2-Si_4$	2.751
	8 <i>c</i>	$C_2(^{1}A)$	511 518	2.050				$Si_2 - Si_4$ $Si_4 - Si_5$	2.583
		- 2( )	$Si_4-Si_5$	2.536				$Si_4-Si_6$	2.525
			$Si_5-Si_6$	2.516				$Si_1-Si_9$	2.370
			$Si_2 - Si_4$	2.503				$Si_8 - Si_9$	2.404
			$Si_1-Si_4$	2.326		9 <i>c</i>	$C_s(^1A)$		
			$Si_2-Si_3$	2.487				$Si_3-Si_7$	2.458
			$Si_1 - Si_3$ $Si_1 - Si_2$	2.511 2.649				$Si_3-Si_6$ $Si_6-Si_7$	2.379 2.656
			$Si_1-Si_2$ $Si_2-Si_7$	2.491				$Si_6 - Si_7$ $Si_5 - Si_6$	2.398
			$Si_3-Si_8$	2.483				$Si_1-Si_6$	2.441
			$Si_7 - Si_8$	2.356				$Si_1-Si_5$	2.567
	8 <i>d</i>	$C_{2v}(^{1}A_{1})$						$Si_1-Si_8$	2.376
			$Si_1-Si_5$	2.535				$\mathrm{Si}_5\mathrm{-Si}_8$	2.283
			$Si_4-Si_5$	2.482				$Si_7 - Si_9$	2.972
			$Si_5-Si_6$	2.425				$Si_1-Si_7$	2.344
			$Si_3-Si_5$	2.695		9 <i>d</i>	$C_{3v}(^{3}A_{2})$	$Si_3-Si_5$	2.464
			$\begin{array}{c} \operatorname{Si}_1 - \operatorname{Si}_2 \\ \operatorname{Si}_2 - \operatorname{Si}_4 \end{array}$	2.380 2.483		ЭU	$C_{3v}(A_2)$	$Si_1-Si_5$	2.493
			$Si_2-Si_4$ $Si_4-Si_6$	2.482				$Si_1-Si_5$ $Si_1-Si_8$	2.334
			$Si_4 Si_6$ $Si_1 - Si_8$	2.320				$Si_1 - Si_3$	2.953
	8e	$D_{3d}(^3A_{1g})$	. 0					$Si_5-Si_6$	2.454
		ū	$Si_1\!-\!Si_4$	2.574	$Si_{10}$	10 <i>a</i>	$C_{3v}(^{1}A_{1})$		
			$Si_1 - Si_7$	2.495				$Si_4-Si_8$	2.760
	0.0	a 345	$Si_1 - Si_6$	2.368				$Si_3-Si_4$	2.491
	8 <i>f</i>	$C_{3v}(^3A_2)$	Q; Q:	2 674				$Si_2-Si_3$	2.547
			$Si_2-Si_4$ $Si_2-Si_3$	2.674 2.536				$ Si_4 - Si_{10} $ $ Si_4 - Si_9 $	2.318 2.460
			$Si_2-Si_3$ $Si_2-Si_5$	2.469				$Si_3-Si_9$	2.434

TABLE I. (Continued.)

Cluster	Isomer	PG (State)	Bond lengt	h (Å)	Cluster	Isomer	PG (State)	Bond len	gth (Å)
	10 <i>b</i>	$T_d(^1A_1)$						$Si_{9}-Si_{10}$	2.674
	100	- a(1)	$Si_4-Si_5$	2.581		11 <i>d</i>	$C_2(^{1}A)$	519 5110	2.07
			$Si_4 - Si_8$	2.354			2( /	$Si_1-Si_2$	2.558
	10c	$C_2(^{1}A)$						$Si_1-Si_3$	2.441
			$Si_4-Si_6$	2.722				$Si_2-Si_3$	2.456
			$Si_4-Si_9$	2.708				$Si_1-Si_5$	2.601
			$Si_2-Si_7$	2.358				$Si_3-Si_6$	2.700
			$Si_1-Si_2$	2.508				$Si_3-Si_7$	2.385
			$Si_1-Si_7$	2.353				$Si_1-Si_8$	2.590
			$Si_5-Si_6$	2.420				$Si_3-Si_8$	2.459
			$Si_3-Si_6$	2.522				Si <sub>1</sub> -Si <sub>9</sub>	2.340
			$Si_3-Si_{10}$	2.695				Si <sub>4</sub> -Si <sub>10</sub>	2.428
			$Si_3-Si_4$	2.311 2.473				Si <sub>5</sub> -Si <sub>10</sub>	2.369 2.504
			$Si_4-Si_{10}$ $Si_1-Si_6$	2.473				$Si_9$ – $Si_{10}$	2.304
			$Si_1-Si_6$ $Si_1-Si_5$	2.791	(b)				
Si <sub>11</sub>	11 <i>a</i>	$C_s(^1A')$	311-315	2.300	Si <sub>11</sub>	11a'	$C_s(^1A')$		
5111	114	C <sub>s</sub> ( 11 )	$Si_1 - Si_2$	2.698	3111	114	$C_s(A)$	$Si_1-Si_2$	2.648
			$Si_1-Si_2$ $Si_2-Si_3$	2.531				$Si_1-Si_2$ $Si_2-Si_3$	2.504
			$Si_3-Si_4$	2.598				$Si_2-Si_3$ $Si_3-Si_4$	2.778
			$Si_1-Si_5$	2.450				$Si_3 Si_4$ $Si_1-Si_5$	2.468
			$Si_3-Si_5$	2.555				$Si_3-Si_5$	2.591
			$Si_3-Si_6$	2.412				$Si_3-Si_6$	2.405
			$Si_1-Si_7$	2.347				$Si_1-Si_7$	2.399
			$Si_1-Si_8$	2.419				$Si_1-Si_8$	2.442
			$Si_3-Si_9$	2.390				$Si_3-Si_9$	2.440
			$Si_3-Si_{11}$	2.483				$Si_3-Si_{11}$	2.493
			$Si_6-Si_7$	2.671				$Si_6-Si_7$	2.686
			$Si_6-Si_9$	2.481				$Si_6 - Si_9$	2.519
			$\mathrm{Si}_6\mathrm{-Si}_{10}$	2.612				$\mathrm{Si}_6\mathrm{-}\mathrm{Si}_{10}$	2.582
			$Si_7 - Si_{10}$	2.369				$Si_7 - Si_{10}$	2.416
			$Si_9 - Si_{10}$	2.468				$Si_9 - Si_{10}$	2.499
	117.	$C_{-}(1A_{-})$	$Si_9 - Si_{11}$	2.365			a (1)	$Si_9 - Si_{11}$	2.391
	11 <i>b</i>	$C_{2v}(^{1}A_{1})$	c: c:	2.501		11b'	$C_{2v}(^1A_1)$	a. a.	0.511
			$Si_2-Si_7$ $Si_3-Si_7$	2.501 2.416				$Si_2-Si_7$	2.511
			$Si_3-Si_7$ $Si_2-Si_5$	2.566				$Si_3-Si_7$	2.434
			$Si_2-Si_5$ $Si_3-Si_4$	2.660				$Si_2-Si_5$ $Si_3-Si_4$	2.594
			$Si_1 - Si_3$	2.479				$Si_3-Si_4$ $Si_1-Si_3$	2.677 2.524
			$Si_1 - Si_9$	2.433				$Si_1-Si_3$ $Si_1-Si_9$	2.463
			$Si_1-Si_{10}$	2.414				$Si_1 - Si_{10}$	2.442
			$Si_9 - Si_{10}$	2.442				$Si_9 - Si_{10}$	2.470
			$Si_1-Si_2$	2.475				$Si_1-Si_2$	2.506
	11 <i>c</i>	$C_s(^1A')$				11 <i>e</i>	$C_s(^1A')$	. 2	
			$Si_2-Si_3$	2.690				$Si_7 - Si_{10}$	2.459
			$Si_3-Si_4$	2.515				$Si_1-Si_7$	2.354
			$Si_1-Si_5$	2.369				$Si_1-Si_2$	2.603
			$Si_3-Si_5$	2.522				$Si_2 - Si_{10}$	2.932
			$Si_2-Si_6$	2.333				$Si_1-Si_7$	2.502
			$Si_3-Si_6$	2.382				$Si_6 - Si_{10}$	2.495
			$Si_1-Si_7$	2.372				$Si_1-Si_5$	2.429
			$Si_1 - Si_8$	2.333				$Si_4-Si_5$	2.667
			$Si_4-Si_8$ $Si_3-Si_9$	2.382 2.401				Si <sub>3</sub> -Si <sub>6</sub>	2.458
			$Si_3-Si_9$ $Si_3-Si_{11}$	2.401				Si <sub>4</sub> -Si <sub>9</sub>	2.480
			$Si_3 - Si_{11}$ $Si_5 - Si_{11}$	2.376				$Si_4-Si_{11}$ $Si_3-Si_4$	2.451 2.503
			$Si_6-Si_7$	2.673				$Si_3 - Si_4$ $Si_1 - Si_4$	2.576
			$Si_6 - Si_9$	2.661				$Si_1 - Si_4$ $Si_9 - Si_{10}$	2.558
			$Si_6 - Si_{10}$	2.447				$Si_5 - Si_{11}$	2.478
			$Si_7 - Si_{10}$	2.480				5 - 11	

stacked distorted rhombi with an additional atom capped on top. 22,45 It can be also viewed as a bicapped pentagonal bipyramid. This lowest-energy structure was predicted by Vasiliev, Ogut, and Chelikowsky 42 and later by other

groups. The isomer  $9b(C_{2v}, {}^1A_1)$ , also a bicapped pentagonal bipyramid (but the two caps are on the same side of the pyramid), is a local minimum. 9b can be obtained via a full geometry optimization starting from the  $(D_{3h}, {}^1A_1)$  tri-

TABLE II. Vibrational frequencies (cm $^{-1}$ ), IR intensities, and zero-point energies of low-energy geometric isomers of  $Si_7 - Si_{11}$ .

Cluster	Isomer	PG (state)	Vibrational frequency (IR intensities)			
Si <sub>7</sub>	7 <i>a</i>	$D_{5h}(^{1}A_{1}^{\prime})$	222.54(0.21)	261.75(0.15)	442 20(10.52)	0.21
	7 <i>b</i>	$C_{3v}(^{1}A_{1})$	232.54(0.21)	261.75(0.15)	443.38(10.52)	0.31
	, -	- 30 (17	131.68(0.03)	186.23(0.02)	242.02(3.25)	0.28
			300.72(2.84)	332.40(0.23)	364.05(0.05)	
			365.61(0.003)	459.62(3.40)	531.29(12.68)	
	7 <i>c</i>	$C_{3v}(^{1}A_{1})$				
			137.84(1.44)	181.66(0.54)	283.53(0.93)	0.31
			301.88(3.01)	332.30(0.91)	368.55(3.93)	
	7.1	a (14)	407.06(10.69)	426.94(3.91)	491.86(25.05)	
	7 d	$C_{2v}(^1A_1)$	28 07(0 02)	100 60(0 22)	100 02(1 12)	0.26
			38.97(0.02) 189.99(0.24)	100.69(0.33) 247.14(1.88)	109.02(1.13) 253.24(0.26)	0.20
			109.99(0.24)	247.14(1.00)	355.39(21.04)	
			329.29(2.76)	335.69(8.44)	376.51(0.14)	
			449.01(13.54)	469.22(0.73)	501.24(2.28)	
Si <sub>8</sub>	8 <i>a</i>	$C_{2h}(^{1}A_{g})$	117.01(13.31)	107.22(0.73)	301.2 ((2.20)	
518	04	0 2n ( 11g)	75.32(0.09)	150.67(0.70)	174.11(0.88)	0.34
			255.47(0.54)	318.59(4.63)	385.50(0.59)	0.5 .
			317.05(2.07)	0 - 0 10 ( 1100)		
			409.01(8.52)	544.93(8.35)		
	8b	$C_{2v}(^{1}A_{1})$	, ,	, ,		
		20 ( 1)	132.26(4.49)	179.77(3.97)	214.29(0.19)	0.35
			222.47(5.60)	254.85(2.00)	261.10(1.42)	
			292.59(0.35)	303.69(0.01)	319.27(3.02)	
			370.52(0.33)	407.71(7.94)	428.76(0.04)	
			445.17(0.2)	477.61(0.50)	498.07(0.38)	
	8 <i>c</i>	$C_2(^{1}A)$				
			90.04(1.39)	123.25(0.02)	172.61(0.21)	0.32
			177.92(0.48)	186.86(1.19)	201.84(0.19)	
			210.49(1.15)	289.20(0.05)	301.71(0.61)	
			325.50(4.87)	330.55(0.54)	338.80(0.001)	
			372.49(5.19)	376.38(0.03)	424.67(10.23)	
		1. ·	461.55(6.35)	488.39(6.84)		
	8 <i>d</i>	$C_{2v}(^1A_1)$	00 50(0 05)	1.15.55(0.001)	4 (2 02 (0 05)	0.00
			92.60(0.35)	145.75(0.001)	162.03(0.97)	0.33
			162.42(0.08)	194.11(2.27)	260.71(1.40)	
			274.41(0.52)	284.94(0.51)	310.04(0.31)	
			340.26(4.13)	362.84(1.39)	385.43(7.05)	
			408.50(0.06) 524.54(24.89)	420.07(7.49)	439.13(9.88)	
	8 <i>e</i>	$D_{3d}(^3A_{1g})$	324.34(24.89)			
	GE.	$D_{3d}(A_{1g})$	135.79(0.53)	308.90(8.10)	323.85(0.02)	0.63
			412.11(4.70)	482.84(3.58)	323.03(0.02)	0.03
	8f	$C_{3v}(^3A_2)$	112.11(11,0)	10210 1(0100)		
	~,	- 30(2)	140.58(0.26)	230.19(0.05)	230.65(0.06)	0.34
			248.87(0.004)	251.79(4.51)	268.42(2.16)	
			322.38(1.66)	345.73(0.55)	386.96(4.96)	
			437.36(4.17)	463.54(5.78)	-/	
	8g	$C_s(^1A')$	` '			
	-		127.07(1.19)	128.32(1.15)	170.27(1.80)	0.34
			185.39(0.44)	221.53(0.04)	221.75(0.47)	
			252.09(1.69)	261.79(1.89)	295.76(0.66)	
			316.11(0.46)	329.26(0.02)	334.85(1.05)	
			357.38(1.64)	399.79(0.12)	425.12(2.62)	
			426.16(1.58)	463.86(0.05)	482.58(4.86)	
		1				
	8h	$D_{2d}(^1A_1)$	145.56(1.59)			
			276.74(4.34)	316.27(0.01)	326.41(1.03)	0.38
a.		a .1	468.87(0.53)	496.35(0.001)	616.34(18.34)	
Si <sub>9</sub>	9 <i>a</i>	$C_{2v}(^1A_1)$	04.06/5.55	440.44(2.22)	450 50/0 5 5	
			91.92(2.29)	119.14(3.33)	172.73(0.96)	0.39
			203.75(4.54)	216.59(1.70)	248.10(0.01)	
			270.59(1.37)	280.11(0.07)	299.67(3.97)	
			305.60(1.57)	323.10(2.83)	338.33(1.50)	
			356.02(1.35)	423.99(1.25)	430.69(0.002)	
	0.5	$C^{-(1_A)}$	452.31(1.47)	488.95(1.96)	498.22(1.76)	
	9b	$C_{2v}(^1A_1)$		165.82(0.001)	150.00(1.00)	0.37
			134.13(0.13)		173.83(1.22)	

 $TABLE\ II.\ (Continued.)$ 

Cluster	Isomer	PG (state)	Vibra	ational frequency (IR inter	nsities)	ZPE (eV
			265.31(2.49)	267.56(0.87)	296.65(0.85)	
			308.31(1.44)	317.82(1.48)	331.62(0.09)	
			367.38(2.02)	369.82(2.65)	408.56(0.004)	
			440.17(6.94)	552.78(1.39)	100.50(0.001)	
	9 <i>c</i>	$C_s(^1A')$				
			70.55(1.38)	107.13(0.22)	162.90(0.15)	0.38
			166.91(1.95)	205.91(0.25)	238.60(3.57)	
			252.71(5.60)	263.56(1.22)	287.39(1.92)	
			295.07(2.84)	304.44(1.97)	308.15(1.37)	
			347.10(0.70)	354.96(0.28)	369.99(1.36)	
			405.09(0.35)	452.67(3.80)	460.95(6.73)	
			487.42(0.13)	514.49(0.16)		
	9 <i>d</i>	$C_{3v}(^{3}A_{2})$				
			100.30(6.84)	113.54(2.35)	179.23(9.29)	0.45
			208.35(0.64)	283.20(1.64)	324.14(0.60)	
			341.40(0.06)	350.19(3.98)	397.04(0.87)	
		1	431.64(3.79)	503.95(10.61)	801.40(523.22)	
Si <sub>10</sub>	10 <i>a</i>	$C_{3v}(^1A_1)$	440.74(4.00)	100 01 (0.15)	220 24/4 25)	0.45
			110.51(1.90)	189.31(0.16)	228.24(1.35)	0.46
			243.64(0.14)	270.09(0.27)	305.10(1.49)	
			316.02(1.06)	318.51(0.18)	341.12(2.00)	
			351.17(4.99)	387.62(0.42)	426.80(0.20)	
	101	T (14 )	459.25(0.02)	510.07(0.32)		
	10b	$T_d(^1A_1)$	98.10(8.03)	203.50(1.91)	299.79(3.46)	0.42
			546.14(22.05)	203.30(1.71)	477.17(3.40)	0.42
	10 <i>c</i>	$C_2(^{1}A)$	J-0.17(22.0J)			
	100	02(11)	101.52(0.01)	103.27(0.15)	116.33(1.78)	0.45
			133.66(0.02)	210.44(1.42)	212.20(0.87)	0.15
			221.85(0.42)	229.57(3.29)	259.72(0.45)	
			264.72(0.26)	286.64(1.55)	295.28(2.08)	
			300.78(0.40)	309.33(0.19)	325.89(0.12)	
			344.38(4.21)	348.26(1.31)	373.22(0.67)	
			383.12(0.39)	395.78(0.50)	440.76(3.84)	
			475.49(0.61)	524.86(1.32)	533.19(1.12)	
Si <sub>11</sub>	11 <i>a</i>	$C_s(^1A')$	.,,		(-11-2)	
			69.40(0.26)	97.15(6.49)	119.32(0.17)	0.48
			124.63(0.54)	140.27(0.83)	177.48(0.11)	
			215.03(1.35)	229.82(0.07)	240.20(7.61)	
			244.78(1.82)	259.02(0.59)	261.36(0.15)	
			280.38(2.71)	289.11(0.59)	295.83(1.67)	
			316.73(4.63)	325.23(1.15)	328.26(0.10)	
			358.32(0.85)	367.64(0.28)	378.00(1.25)	
			392.65(0.002)	412.75(10.72)	429.90(5.09)	
			432.35(1.94)	470.02(4.49)	517.23(9.70)	
	11b	$C_{2v}(^{1}A_{1})$				
			104.53(1.17)	134.20(2.19)	136.35(3.31)	0.48
			153.96(4.23)	164.43(0.73)	177.84(0.87)	
			222.28(0.78)	229.28(0.15)	259.98(1.50)	
			270.32(2.25)	291.92(0.48)	304.56(7.21)	
			320.46(0.05)	335.13(0.01)	336.64(0.82)	
			344.59(8.56)	374.74(0.03)	388.99(0.39)	
			432.26(0.37)	432.74(0.01)	472.00(6.56)	
			496.16(18.95)	519.60(22.37)		
	11 <i>c</i>	$C_s(^1A')$				
			51.32(2.61)	69.05(0.61)	106.88(0.17)	0.47
			114.82(2.59)	129.32(2.43)	163.01(0.50)	
			164.29(0.54)	201.17(0.87)	225.80(0.06)	
			228.96(0.69)	238.83(1.73)	241.71(1.10)	
			262.43(2.53)	285.86(0.15)	287.24(0.23)	
			304.84(0.74)	341.84(0.03)	364.25(0.09)	
			368.26(5.43)	386.66(2.20)	390.20(0.002)	
			401.69(11.69)	427.14(0.29)	431.83(6.47)	
	11.1	a (14)	446.87(2.88)	483.25(2.27)	504.03(12.67)	
	11 <i>d</i>	$C_2(^1A)$	68.90(0.82)	88.65(0.47)	109.24(0.53)	0.47
			06.90(0.82)	00.03(0.47)	109.24(0.33)	0.4/

TABLE II. (Continued.)

Cluster	Isomer	PG (state)	Vibrat	Vibrational frequency (IR intensities)			
			219.95(0.05)	228.05(0.05)	252.04(0.91)		
			252.39(1.46)	260.18(0.85)	262.62(4.36)		
			279.70(1.57)	284.32(2.10)	305.01(1.14)		
			310.71(0.12)	314.60(0.32)	329.07(1.33)		
			335.36(0.98)	348.85(0.08)	368.54(0.27)		
			380.61(3.94)	463.57(11.86)	483.36(9.54)		
			524.65(30.37)	527.53(4.02)			

capped trigonal prism (TTP). Previously, Lee, Chang, and Lee<sup>35</sup> and also Luo, Zhao, and Wang<sup>43</sup> reported that the isomer  $9b(C_{2v}, {}^{1}A_{1})$  was a possible global minimum based on semiempirical methods.

At the MP2/6-31G(d) level, the vibrational frequency analysis indicates that the distorted TTP ( $C_{2v}$ ,  $^1A_1$ ) (Ref. 22) is unstable. However, it has been shown that the distorted TTP ( $C_{2v}$ ) isomer, although unstable at the MP2/6-31G(d) level, can be a favorable structural motif in some larger silicon clusters. The distorted tricapped octahedron ( $C_s$ ,  $^1A'$ ) (Refs. 27, 28, and 31) is also found unstable at the MP2/6-31G(d) level as it transforms into  $9c(C_s$ ,  $^1A'$ ), another form of distorted tricapped trigonal prism (TTP), in a full geometry optimization. To our knowledge, the distorted TTP ( $C_s$ ,  $^1A'$ ) isomer has not been reported in the literatures. The tricapped octahedron in triplet state,

 $9d(C_{3v}, {}^{3}A_{2})$ , is a relatively high-energy local minimum, as predicted by Raghavachari and Kohlfing.<sup>27</sup>

#### 4. N=10

 $\mathrm{Si}_{10}$  is a magic-number cluster which has been extensively studied theoretically.  $^{27,28,30,31,35,36,38-40,43,45}$  Our calculation confirms that the isomer  $10a(C_{3v}, {}^1A_1)$ , a *tetracapped trigonal prism*, is the global minimum, as already predicted by many other groups.  $^{28,31,36,38,40}$  The isomer  $10b(T_d, {}^1A_1)$ , a tetracapped octahedron, is a low-energy local minimum as shown by Raghavachari and Kohlfing.  $^{27}$  The isomer  $10c(C_2, {}^1A)$ , obtained via a full geometry optimization from the geometric isomer  $10k(C_s)$  in Ref. 40, is a new low-energy isomer that not has been reported in the literatures. Its energy is close to that of the isomer 10b.

TABLE III. The energy separations for low-energy isomers of Si<sub>7</sub>-Si<sub>11</sub>.

Cluster	Isomer	PG (state)	MP2/6-31G( <i>d</i> ) (eV)	CCSD(T)/6-31G( <i>d</i> ) (eV)	MP2/6-311(2 <i>d</i> ) (eV)	CCSD(T)/6-311(2d) (eV)
Si <sub>7</sub>						
	7 <i>a</i>	$D_{5h}(^{1}A_{1}^{\prime})$	0.00	0.00		
	7 <i>b</i>	$C_{3v}(^{1}A_{1})$	0.93	0.67		
	7 <i>c</i>	$C_{3v}(^{1}A_{1})$	2.17	1.71		
	7d	$C_{2v}(^{1}A_{1})$	2.63	2.21		
$Si_8$						
	8 <i>a</i>	$C_{2h}(^{1}A_{g})$	0.00	0.00		
	8b	$C_{2v}(^{1}A_{1})$	0.31	0.19		
	8c	$C_2(^{1}A)$	0.58	0.52		
	8d	$C_{2v}(^{1}A_{1})$	0.41	0.55		
	8e	$D_{3d}(^{3}A_{1g})$	0.68	0.58		
	8f	$C_{3v}(^{3}A_{2})$	0.95	0.60		
	8g	$C_s(^1A')$	0.52	0.62		
	8h	$D_{2d}(^{1}A_{1})$	1.00	1.73		
$Si_9$						
	9 <i>a</i>	$C_{2v}(^{1}A_{1})$	0.00	0.00		
	9 <i>b</i>	$C_{2v}(^{1}A_{1})$	0.60	0.74		
	9 <i>c</i>	$C_s(^1A')$	1.28	1.24		
	9 <i>d</i>	$C_{3v}(^{3}A_{2})$	2.07	1.60		
$Si_{10}$						
	10 <i>a</i>	$C_{3v}(^{1}A_{1})$	0.00	0.00		
	10b	$T_d(^1A_1)$	1.99	0.75		
	10c	$C_2(^{1}A)$	1.27	0.81		
$Si_{11}$						
	11 <i>a</i>	$C_s(^1A')$	0.00	0.00	0.00(11a')	0.09(11a')
	11 <i>b</i>	$C_{2v}(^{1}A_{1})$	0.53	0.02	0.40(11b')	0.00(11b')
	11 <i>c</i>	$C_s(^1A')$	0.21	0.22		
	11 <i>d</i>	$C_2(^{1}A)$	0.87	0.53		
	11 <i>e</i>	$C_s(^1A')$			0.00	0.03

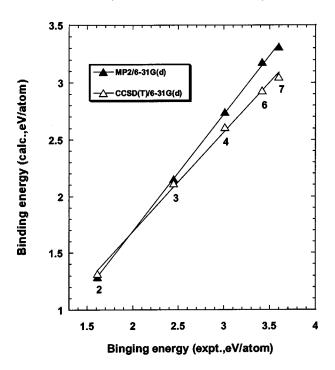


FIG. 2. Correlation of the calculated binding energies per atom and measured values for the low-energy isomers of  $Si_n$  (n = 2-4,6-7).

#### 5. N=11

Si<sub>11</sub> deserves more discussion because the globalminimum structure of Si<sub>11</sub> was not fully conclusive due to the existence of multiple nearly degenerate low-energy isomers.  $^{28,35,38,39,45}$  In fact,  $\mathrm{Si}_{11}$  can be a good model system for testing theoretical methods. At the MP2/6-31G(d) level we found that the  $D_{3h}$  pentacapped trigonal prism is unstable, although it is a stable structure when calculated at the HF/6-31G(d) level.<sup>28</sup> Table III lists the total energy of three nearly isoenergetic geometric isomers calculated at the MP2/6-31G(d)//CCSD(T)/6-31G(d) level, 11a( $C_s$ ,  ${}^1A'$ ), a distorted tricapped tetragonal antiprism or a distorted pentacapped trigonal prism,  $11b(C_{2v}, {}^{1}A_{1})$ , a tricapped trigonal prism with two additional caps on side trigonal faces, and  $11c(C_s, {}^1A')$ , a bicapped tetragonal antiprism with an additional cap on one upper trigonal face. Among the three isomers,  $11a(C_s, {}^1A')$  was proposed by Lee, Chang, and Lee<sup>35</sup> and also later by Sieck et al.;<sup>45</sup>

TABLE IV. Binding energies per atom calculated at the MP2/6-31G(d) and CCSD(T)/6-31G(d) levels compared with available experimental data.

Cluster		Bindi	ng energy (eV/atom)	
(isomer)	Point group	MP2/6-31G(d)	CCSD(T)/6-31G(d)	Expt.a
Si <sub>2</sub>	$D_{\infty h}$	1.29	1.32	1.61
$Si_3$	$C_{2n}$	2.15	2.11	2.45
Si <sub>4</sub>	$D_{2h}$	2.74	2.61	3.01
Si <sub>6</sub>	$D_{4h}$	3.18	2.93	3.42
$Si_7(7a)$	$D_{5h}$	3.31	3.05	3.60
$Si_8(8a)$	$C_{2h}$	3.20	2.95	
$Si_9(9a)$	$C_{2v}$	3.33	3.04	
$Si_{10}(10a)$	$C_{3v}$	3.50	3.14	
Si <sub>11</sub> (11 <i>a</i> )	$C_s$	3.40	3.08	

<sup>&</sup>lt;sup>a</sup>Reference 31.

 $11b(C_{2v}, {}^{1}A_{1})$  and  $11c(C_{s}, {}^{1}A')$  were predicted by Rohlfing and Raghavachari<sup>28</sup> based on the HF/6-31G(d)//MP4SDQ/6-31G(d) calculation. The isomer  $11b(C_{2v}, {}^{1}A_{1})$ was also predicted to be a possible global minimum by Ho and coworkers<sup>39</sup> using a density-functional pseudopotential theory within both local density and generalized gradient approximations;  $11a(C_s, {}^1A')$  [Cs(II) in Ref. 39] was predicted to be a local minimum. Ho and co-workers<sup>39</sup> recently used Car-Parrinello molecular dynamics combined with the simulated annealing method to search for the global-minimum structure of Si<sub>11</sub>. They found again that 11b is most likely the global minimum. At the MP2/6-31G(d)//CCSD(T)/6-31G(d) level, we found that both isomers 11a and 11b are the possible global minimum while 11c is only about 0.2 eV higher in energy than 11a and 11b. The isomer  $11d(C_2, {}^1A)$ , another capped trigonal prism, is a new low-energy isomer whose energy is 0.53 eV higher than that of 11a.

The fact that Si<sub>11</sub> has at least three possible candidates for the global-minimum structure on the basis of MP2/6-31G(d)//CCSD(T)/6-31G(d) calculation prompts us to further examine the relative stability of these three geometric isomers with a larger basis set. We chose MP2/6-311G(2d)//CCSD(T)/6-311G(2d) levels for which our current computer facility can afford. The full geometry optimization at the MP2/6-311G(2d) level reveals that the previously optimized structure of 11a and 11b remains nearly unchanged [the newly optimized structures, called  $11a'(C_s, {}^1A_1)$  and  $11b'(C_{2v}, {}^1A_1)$ , are given in Table I(b)]. However, significant structural change occurred for the isomer  $11c(C_s, {}^1A')$ . The newly optimized structure starting from 11c is hereafter called  $11e(C_s, {}^1A')$ , which is also a capped trigonal prism. The structural data of 11e is shown in Table I(b). The calculated single-point energies for 11a', 11b', and 11e at both the MP2/6-311G(2d) and CCSD(T)/6-311G(2d) levels are listed in Table III. At the MP2/6-311G(2d) level, now both  $11a'(C_s, {}^1A')$  and  $11e(C_s, {}^1A')$  are the two lowest-energy structures, whereas at the CCSD(T)/6-311G(2d) level  $11b'(C_{2v}, {}^{1}A_{1})$  becomes the global minimum but  $11e(C_s, {}^1A')$  is merely 0.03 eV higher in energy than 11b'. It can be also seen from Table III that the use of the larger basis set at the MP2 level [6-311G(2d)] results in a smaller energy difference between 11b' and 11a', compared to that between 11b and 11a at the MP2/6-31G(d) level, while at the CCSD(T)/6-311G(2d) level 11b' becomes the global minimum. From this trend, it appears that the isomer 11b' would be more energetically favorable if an even larger basis set [e.g., 6-311(3df)] were used. Note that the difference in the zero-point vibrational energy for the three geometric isomers is less than 0.01 eV (see Table II). Therefore, including zeropoint vibrational energy in the total energy will not qualitatively affect the energy ordering among the three nearly isoenergetic isomers. Note also that the structure of newly obtained  $11e(C_s, {}^1A')$  does not resemble that of Cs(I) isomer reported in Ref. 39, which was predicted to be another possible global minimum of Si<sub>11</sub> [the Cs(I)'s geometric structure resembles that of  $C_{2v}$  11b].<sup>59</sup>

To summarize, our calculations at both the MP2 and

CCSD(T) levels consistently reproduce all the global-minimum structures of  $\mathrm{Si}_7\mathrm{-Si}_{10}$  reported in the literature. For  $\mathrm{Si}_{11}$ , however, the predicted global-minimum structure is different on the basis of the MP2 level and the CCSD(T) level. The CCSD(T)/6-311G(2d) calculation indicates that the isomer  $11b'(C_{2v}, {}^1A_1)$  is the global minimum, but also shows that  $11e(C_s, {}^1A')$  is a very competitive candidate for the global minimum.

#### B. Cluster growth feature

As shown in Fig. 1, the pentagonal bipyrimid, tetrahedron, distorted octahedron, and tricapped trigonal prism (TTP) all could be viewed as motifs for low-energy structures of  $Si_7-Si_{11}$ . For example, the isomer  $7a(D_{5h}, {}^1A_1')$ appears to be such a motif due to its high stability. Lowenergy clusters such as 8d, 8g, 9a, and 9b can be constructed via capping 7a on edges or faces. The distorted octahedron is the global minimum of Si<sub>6</sub>. <sup>20,25</sup> When capped on edges or faces, it becomes clusters 7c, 7d, 8e, 8h, 9d, or 10b. Although the tetrahedron (Si<sub>4</sub>) is not a stable structure itself due to large strain energy,<sup>27</sup> it can also be viewed as a building block for some low-energy structures (e.g., 7b and 8f) when its faces are properly capped. Moreover, the TTP in triplet state is a local minimum of Si<sub>9</sub>, but it has a higher energy compared to many other low-energy isomers. Nevertheless, it can be viewed as a motif for some lowenergy structures of  $Si_{11}$  (11a-11e) and even some larger  $\operatorname{Si}_n$  (n=12-26) clusters<sup>21</sup> as well.

A common feature in small silicon clusters  $\mathrm{Si}_7 - \mathrm{Si}_{11}$  is that the lowest-energy structures are all spherical-like. The spherical-like shape minimizes the surface area and reduces the number of dangling bonds. The low-energy structures of  $\mathrm{Si}_7$ , for example, deviate gradually from spherical-like shape, as the energy increases from isomer 7a to 7d (see Table III), indicating that the more spherical-like isomer 7a is more energetically favorable. This deviation from spherical-like shape (7a to 7d) is also manifested in their dipole moments (see Table V). As shown in Fig. 3, the binding energy per atom for the lowest-energy structure of  $\mathrm{Si}_n$  (n=2-11) increases with  $n^{-1/3}$ , supporting the spherical-like cluster growth. For nonspherical-like (prolate) cluster growth, the binding energy per atom would be nearly independent of the size of cluster.

In most cases, if clusters favor spherical-like shape the lowest-energy structures of the clusters tend to have high degree of symmetry. However, high symmetrical clusters with incomplete electronic shells can be even more stabilized through a geometry deformation which results in a lower degree of symmetry. As an example, the lowest-energy structure of  $Si_8$  does not exhibit cubic symmetry with the  $O_h$  point group. Rather, it exhibits  $C_{2h}$  symmetry due to Jahn–Teller distortion, similar to the cases of  $Si_4$  (Ref. 27) and  $Si_6$  (Ref. 20). For  $Si_9$ , the global minimum is 9a with  $C_{2v}$  symmetry; it can be derived from the distortion of tricapped octahedron ( $C_{3v}$ ) in singlet state.

TABLE V. Dipole moments of low-energy isomers of  $Si_7$ – $Si_{11}$  at the MP2/6-31G(d) level.

Cluster	Isomer	PG (state)	$\mu(D)$
Si <sub>7</sub>	7 <i>a</i>	$D_{5h}(^{1}A'_{1})$	0.000
	7 <i>b</i>	$C_{3v}(^{1}A_{1})$	1.518
	7 c	$C_{3v}(^{1}A_{1})$	1.602
	7 <i>d</i>	$C_{2v}(^{1}A_{1})$	1.639
Si <sub>8</sub>	8 <i>a</i>	$C_{2h}(^{1}A_{g})$	0.000
	8b	$C_{2v}({}^{1}A_{1})$	0.611
	8 <i>c</i>	$C_2(^{1}A)$	1.360
	8 <i>d</i>	$C_{2v}(^{1}A_{1})$	1.929
	8 <i>e</i>	$D_{3d}(^{3}A_{1g})$	0.000
	8f	$C_{3v}(^{3}A_{2})$	0.324
	8g	$C_s(^1A')$	0.880
	8h	$D_{2d}(^{1}A_{1})$	0.000
Si <sub>9</sub>	9 <i>a</i>	$C_{2v}(^{1}A_{1})$	0.430
	9b	$C_{2v}(^{1}A_{1})$	1.216
	9 <i>c</i>	$C_s(^1A')$	1.235
	9 <i>d</i>	$C_{3v}(^{3}A_{2})$	0.897
$Si_{10}$	10 <i>a</i>	$C_{3v}(^{1}A_{1})$	1.101
	10b	$T_d(^1A_1)$	0.000
	10c	$C_2(^{1}A)$	1.148
Si <sub>11</sub>	11 <i>a</i>	$C_s(^1A')$	1.258
	11 <i>b</i>	$C_{2v}(^{1}A_{1})$	2.098
	11 <i>c</i>	$C_s(^1A')$	2.288
	11 <i>d</i>	$C_2(^1A)$	1.215

#### C. Energy and stability

It can be seen from Table III that the lowest-energy structures of  $Si_7-Si_{11}$  all have *closed-shell* structures. It is known that the CCSD(T) level of theory<sup>52,56-58</sup> is more accurate in estimating electron correlation than the MP2 level. In many cases, the CCSD(T) level yields only small quantitative changes in the relative energy of geometric isomers. For instance, isomers 7b and 7c of  $Si_7$  are higher in energy

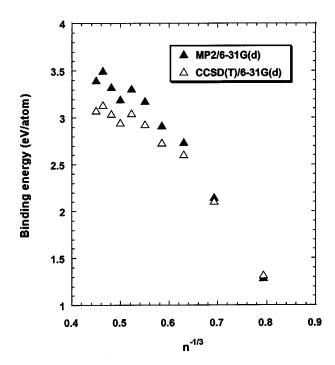


FIG. 3. Correlation of binding energy per atom and  $n^{-1/3}$  for the low-energy isomers of  ${\rm Si}_2{-}{\rm Si}_{11}$  .

than 7a by 0.93 and 2.17 eV at the MP2/6-31G(d) level, but at the CCSD(T)/6-31G(d) level, 7b and 7c are 0.67 and 1.71 eV higher than 7a. However, for some isomers of Si<sub>7</sub>-Si<sub>11</sub> the CCSD(T) level can qualitatively affect the relative energy, that is, the MP2/6-31G(d) energy ordering can be different from the CCSD(T)/6-31G(d) one. This shows the importance of having accurate electron-correlation energy in the determination of the relative stability for geometric isomers with very close energy, for example, the three nearly isoenergetic isomers of Si<sub>11</sub>.

The ionization potentials (IPs) can also be used to evaluate the relative stability of isomers. In principle, cluster IP should decrease gradually towards the work function of bulk phase as the size of clusters increase. In the case of metal clusters, 47 the classical conducting spherical droplet (CSD) model suggests a linear IP versus  $n^{-1/3}$  relationship, which can reproduce many experimental IPs quite well. However, the experimental IPs of  $Si_n$  (n=2-200) deviate notably from the CSD model. 47 We cannot offer a theoretical explanation for this deviation because of the limited size range of  $Si_n$  (n=7-11) considered here. But we have found an agreement between the calculated vertical ionization potentials (VIP) and measured values<sup>48</sup> for Si<sub>2</sub>-Si<sub>11</sub>, as shown in Table VI. It is interesting to note that there is a large gap between n=20 and n=22 in the photoionization threshold measurements of  $Si_n$  (n=2-400), <sup>49</sup> which might imply a possible structural transition in this size range of silicon clusters. An ab initio molecular-orbital study for this size range of Si clusters is under way.

It is known that some simple-metal clusters are "magic-number" clusters  $^{32}$  when the number of valence electrons in the clusters is 8, 20, 40, or 58 etc. The magic-number clusters can be understood on the basis of particle-in-box model or jellium model. The "magic-number" behavior of small silicon clusters has been correlated with the trend of binding energy per atom as a function of cluster size. Luo, Zhao, and Wang pointed out that two factors can play major role in the cluster stability, one is the electronic configuration of an atom and another is the number of atoms in the cluster. Here, the binding energies of the lowest-energy structures of  $Si_2-Si_{11}$  are calculated at the MP2/6-31G(d) and CCSD(T)/6-31G(d) level, as shown in Table IV. Figure 4

TABLE VI. Vertical ionization potentials of the lowest-energy isomer of  $\mathrm{Si}_{7}\text{-}\mathrm{Si}_{11}$  .

Cluster	Isomer	PG (state)	IP (calc.) (eV)	IP (expt.) <sup>a</sup> (eV)
Si <sub>2</sub>		$D_{\infty h}$	7.87	>8.49
Si <sub>3</sub>		$C_{2v}$	7.88	>8.49
Si <sub>4</sub>		$D_{2h}^{2b}$	8.09	7.97-8.49
Si <sub>5</sub>		$D_{3h}^{2n}$	8.02	7.97 - 8.49
Si <sub>6</sub>		$D_{4h}^{sh}$	7.84	7.97-8.49
Si <sub>7</sub>	7 <i>a</i>	$D_{5h}^{4h}(^{1}A_{1}^{\prime})$	7.86	~7.90
Si <sub>8</sub>	8 <i>a</i>	$C_{2h}(^{1}A_{g})$	7.16	7.46-7.87
Si <sub>9</sub>	9 <i>a</i>	$C_{2v}^{2n}(^{1}A_{1}^{s})$	7.53	7.46-7.87
Si <sub>10</sub>	10a	$C_{3v}^{2v}(^{1}A_{1})$	7.95	~7.90
Si <sub>11</sub>	11 <i>a</i>	$C_s(^1A')$	7.03	7.46-7.87

aReference 50.

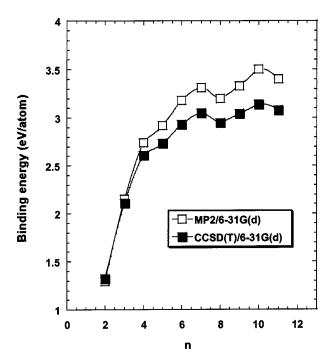


FIG. 4. Binding energy per atom of the lowest-energy structures of  $Si_2-Si_{11}$  vs cluster size n.

plots the binding energies per atom versus the number of Si atoms n. A notable decrease in the slope of the curve can be seen at the cluster size of  $Si_4$ ,  $Si_7$ , and  $Si_{10}$ .

As pointed out by Raghavachari and Rohlfing,<sup>27</sup> a better way to show the relative local stability of small silicon clusters is through the use of the incremental binding energy as a function of cluster size. The incremental binding energy can be defined as  $(E_{n-1}+E_1)-E_n$ , where  $E_n$  is the single-point total energy of cluster Si<sub>n</sub>. Figure 5 shows the calculated incremental binding energy versus cluster size n at both

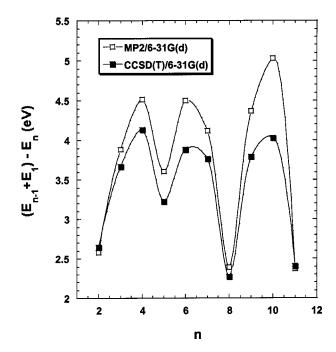


FIG. 5. Incremental binding energy of  $Si_2-Si_{11}$  clusters vs cluster size n.

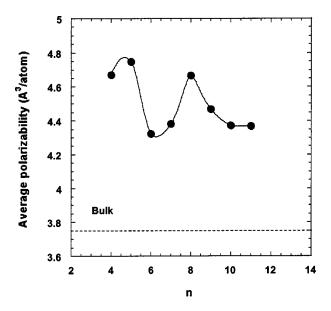


FIG. 6. Average polarizability for the lowest-energy structures of  $Si_4$ - $Si_{11}$  as a function of cluster size n.

MP2/6-31G(d) and CCSD(T)/6-31G(d) levels. Clearly, the local maximum in the incremental binding energy corresponds to the cluster Si<sub>4</sub>, Si<sub>6</sub>, and Si<sub>10</sub>. For the latter, the marked local stability together with the fact that Si<sub>10</sub> has the highest binding energy compared to other small silicon clusters provide reasonable explanation why Si<sub>10</sub> is a magic-number cluster with exceptional stability.

The cluster polarizability stems mainly from the surface electron density of the cluster.  $^{42}$  As mentioned above, smaller clusters have a larger surface/interior atom ratio. For  $\mathrm{Si}_7{-}\mathrm{Si}_{11}$ , nearly all atoms are on the surface of the clusters. Thus, the polarizability of these clusters is expected to be larger than that of the bulk. In addition, the unsaturated bonds at the cluster surface will make polarizabilities even larger. In Fig. 6, results are shown for the size dependence of mean polarizability for  $\mathrm{Si}_4{-}\mathrm{Si}_{11}$ . The relatively strong stability of the magic-number cluster  $\mathrm{Si}_6$  and  $\mathrm{Si}_{10}$  seems to correlate well with the local minimum in the cluster polarizability versus n.

#### **IV. CONCLUSIONS**

We have obtained optimized geometries of a number of low-energy geometric isomers of Si<sub>7</sub>-Si<sub>11</sub> at the MP2/6-31G(d)level and their energy at CCSD(T)/6-31G(d) level. For  $Si_{11}$ , a larger basis set with both levels of theory, MP2/6-311G(2d)CCSD(T)/6-311G(2d), were also employed. In most cases the electron-correlation effects on geometries of clusters are only quantitative, compared to geometries obtained at the HF/6-31G(d) level. In some cases, the electron-correlation effects can be qualitative. This is particularly important for Si<sub>11</sub>. The calculated binding energies and vertical ionization potentials for the lowest-energy structures of Si<sub>7</sub>-Si<sub>11</sub> are in agreement with experimental values. The binding energy per atom has an  $n^{-1/3}$  dependence, suggesting that small silicon clusters favors spherical-like cluster growth. A few new lowenergy geometric isomers are found for these silicon clusters. Among them, a new candidate for the global minimum of  $Si_{11}$  is identified. The relatively strong stability of magic-number clusters  $Si_n$  (n=6 and 10) appears to correlate well with their relatively higher binding energy per atom, their local-maximum feature in the incremental binding energy and their local-minimum feature in the cluster polarizability vs the cluster size n.

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